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Modeling of 3D silicon detectors

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The transient response of 3D detectors has been modeled using TCAD. Experimental results (testbeam and in laser experiments) show a negative peak observed from a neighbouring pixel to the pixel in which the mip passes . This response is shown and explained The simulation is performed for CNM double sided devices and full 3d detectors. The simulation will be extended to understand the response of the detector after irradiation with a plan to understand charge multiplication.

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